

## General Description

FSMOS<sup>®</sup> MOSFET is based on Oriental Semiconductor's unique device design to achieve low  $R_{DS(ON)}$ , low gate charge, fast switching and excellent avalanche characteristics. The high  $V_{th}$  series is specially optimized for high systems with gate driving voltage greater than 10V.

## Features

- Low  $R_{DS(ON)}$  & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery



## Applications

- Switching mode power supply
- Motor driver
- Battery protection
- DC-DC convertor
- Solar inverter
- UPS and energy inverter

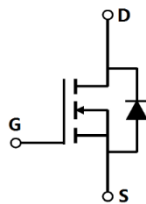
## Key Performance Parameters

Parameter	Value	Unit
$V_{DS}$	60	V
$I_D$ , pulse	390	A
$R_{DS(ON)}$ , max @ $V_{GS}=10V$	3.5	m $\Omega$
$Q_g$	56.8	nC
PD	140	W

## Marking Information

Product Name	Package	Marking
SFS130N06DF	TO252	SFS130N06D

## Package & Pin information



**Absolute Maximum Ratings** at  $T_j=25^{\circ}\text{C}$  unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	$V_{DS}$	60	V
Gate source voltage	$V_{GS}$	$\pm 20$	V
Continuous drain current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$	$I_D$	130	A
Pulsed drain current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$	$I_{D, pulse}$	390	A
Continuous diode forward current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$	$I_S$	130	A
Diode pulsed current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$	$I_{S, Pulse}$	390	A
Power dissipation <sup>3)</sup> , $T_C=25^{\circ}\text{C}$	$P_D$	140	W
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	94	mJ
Operation and storage temperature	$T_{stg}, T_j$	-55 to 150	$^{\circ}\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.89	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient <sup>4)</sup>	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$

**Electrical Characteristics** at  $T_j=25^{\circ}\text{C}$  unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	$BV_{DSS}$	60			V	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	2		4	V	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$
Drain-source on-state resistance	$R_{DS(ON)}$		3.3	3.5	$\text{m}\Omega$	$V_{GS}=10\text{ V}, I_D=20\text{ A}$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS}=20\text{ V}$
				-100		$V_{GS}=-20\text{ V}$
Drain-source leakage current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS}=60\text{ V}, V_{GS}=0\text{ V}$
Gate resistance	$R_G$		2.5		$\Omega$	$f=1\text{ MHz}$ , Open drain

### Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	$C_{iss}$		5411		pF	$V_{GS}=0\text{ V}$ , $V_{DS}=25\text{ V}$ , $f=100\text{ KHz}$
Output capacitance	$C_{oss}$		1522		pF	
Reverse transfer capacitance	$C_{rss}$		24.2		pF	
Turn-on delay time	$t_{d(on)}$		31.4		ns	$V_{GS}=10\text{ V}$ , $V_{DS}=50\text{ V}$ , $R_G=2\ \Omega$ , $I_D=50\text{ A}$
Rise time	$t_r$		54.8		ns	
Turn-off delay time	$t_{d(off)}$		60.5		ns	
Fall time	$t_f$		112.5		ns	

### Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	$Q_g$		56.8		nC	$V_{GS}=10\text{ V}$ $V_{DS}=50\text{ V}$ , $I_D=50\text{ A}$ ,
Gate-source charge	$Q_{gs}$		17.8		nC	
Gate-drain charge	$Q_{gd}$		6.3		nC	
Gate plateau voltage	$V_{plateau}$		4.4		V	

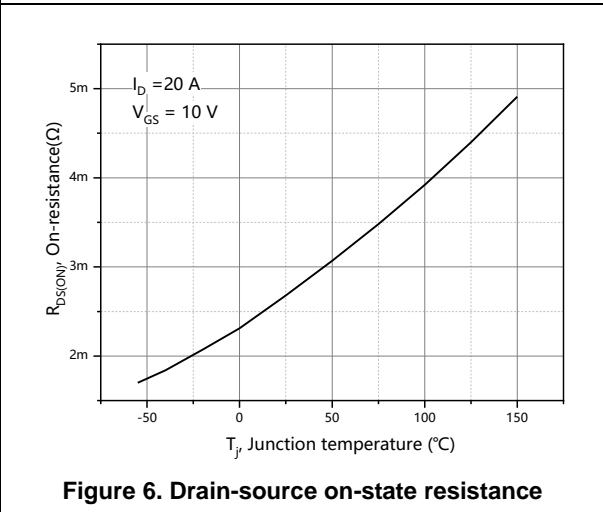
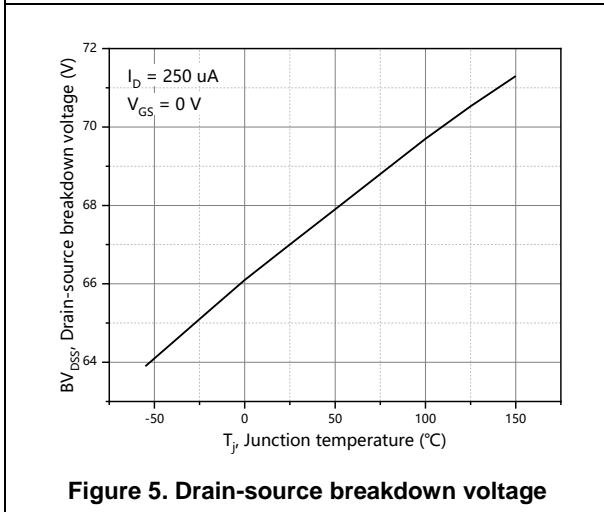
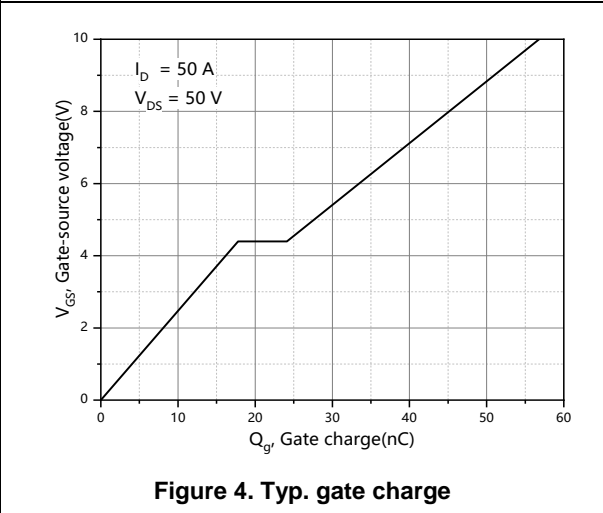
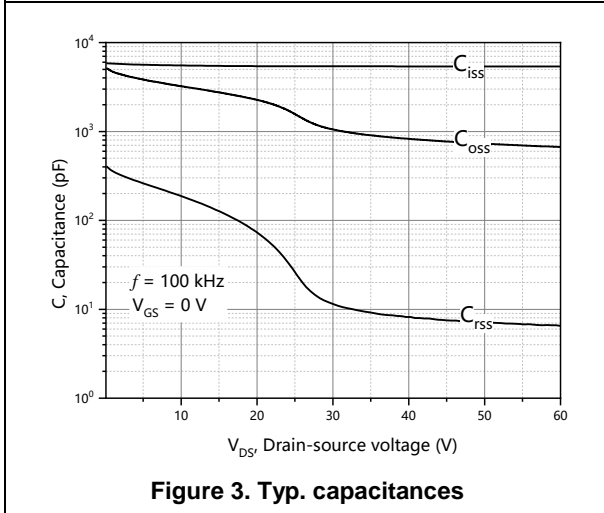
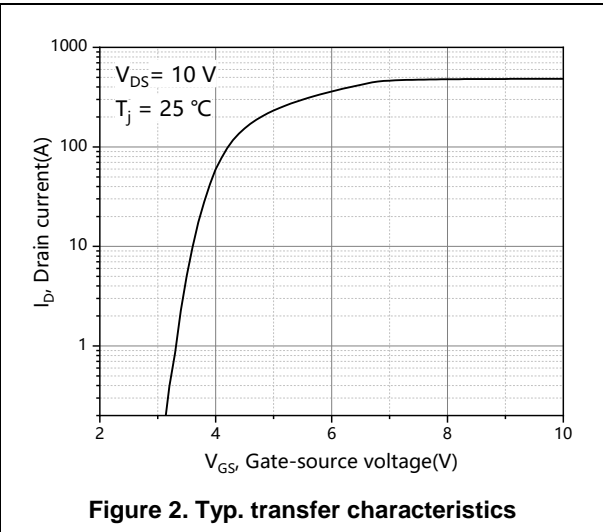
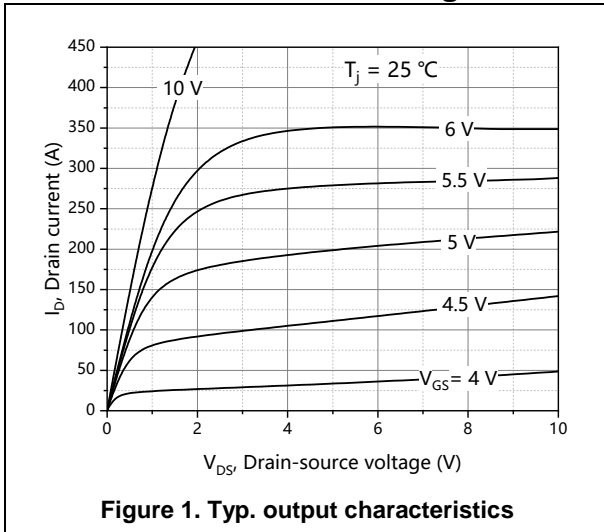
### Body Diode Characteristics

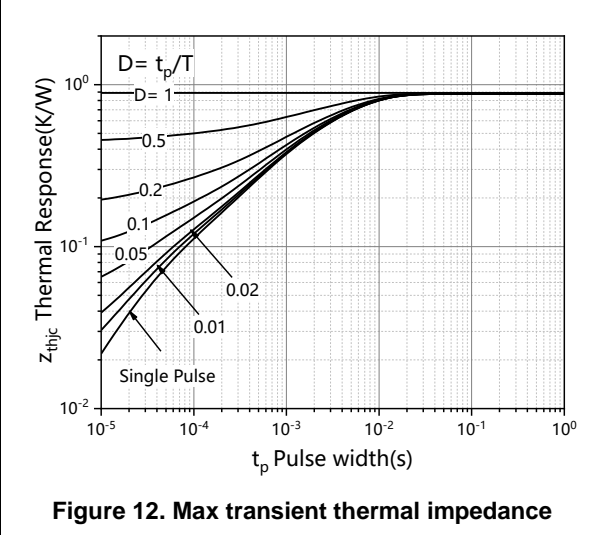
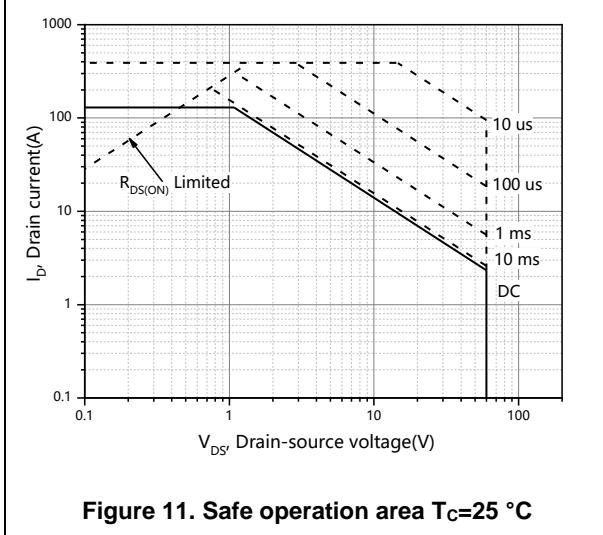
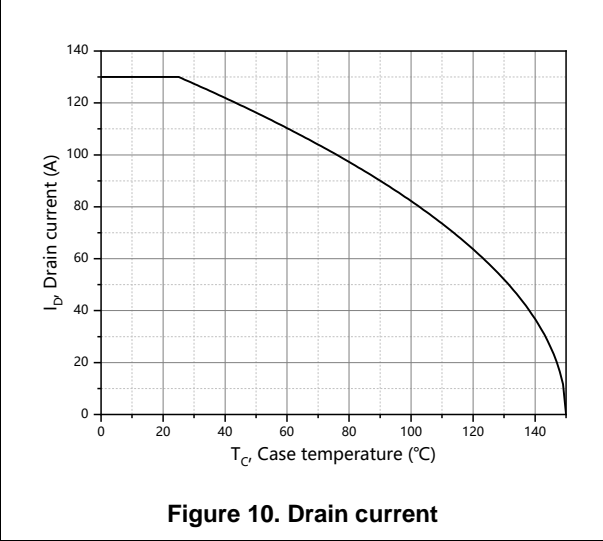
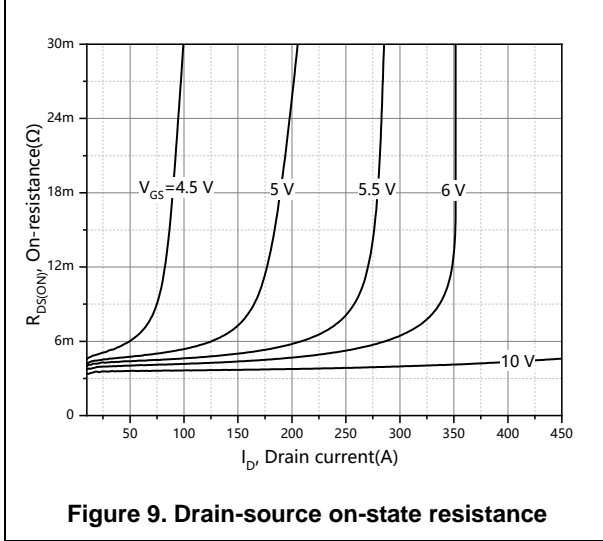
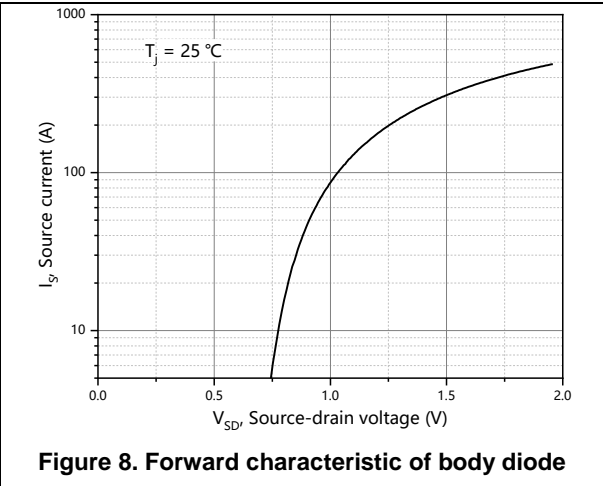
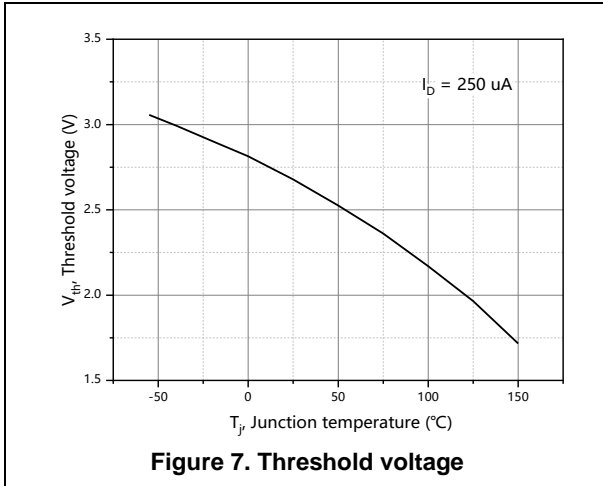
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	$V_{SD}$			1.3	V	$I_S=20\text{ A}$ , $V_{GS}=0\text{ V}$
Reverse recovery time	$t_{rr}$		70		ns	$V_R=50\text{ V}$ , $I_S=50\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		95		nC	
Peak reverse recovery current	$I_{rrm}$		2.6		A	

### Note

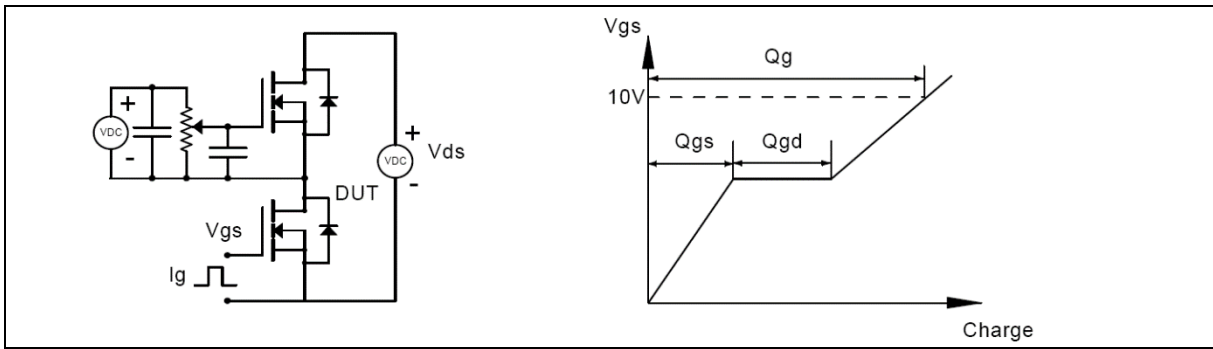
- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=30\text{ V}$ ,  $V_{GS}=10\text{ V}$ ,  $L=0.3\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

**Electrical Characteristics Diagrams**

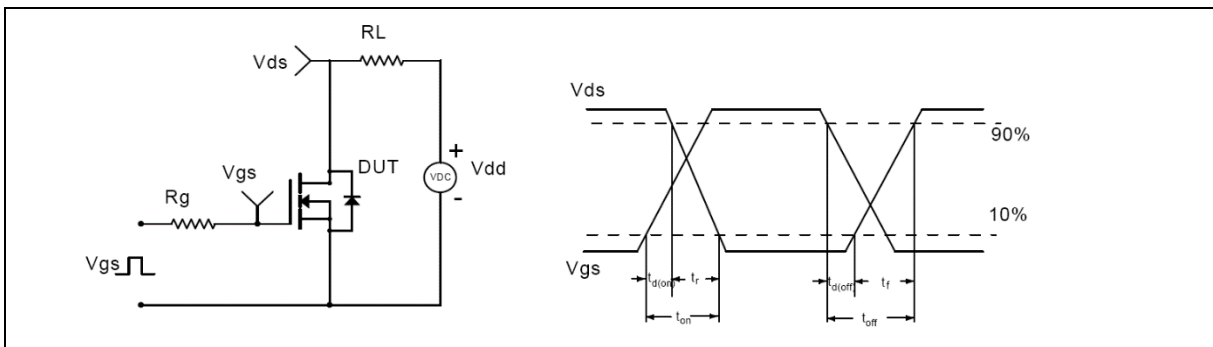




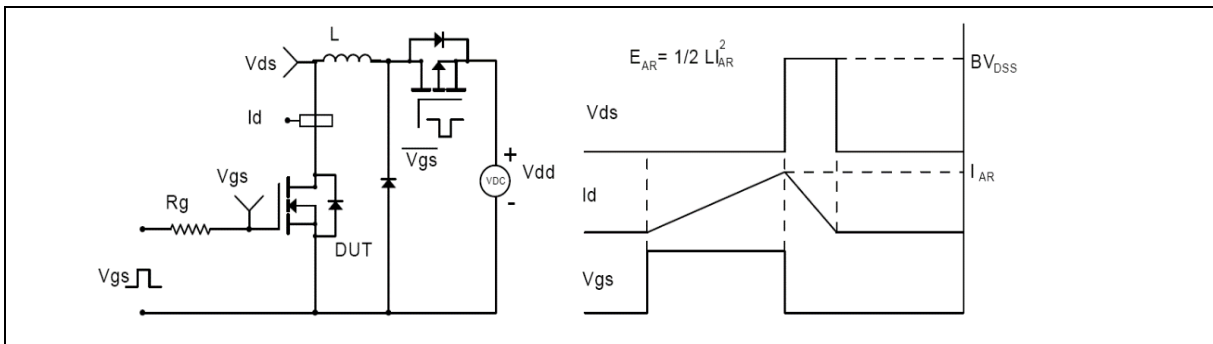
**Test circuits and waveforms**



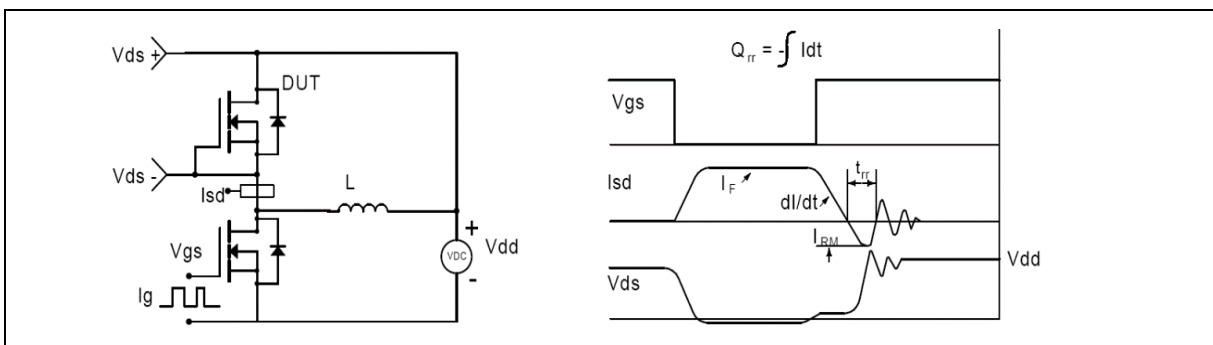
**Figure 1. Gate charge test circuit & waveform**



**Figure 2. Switching time test circuit & waveforms**



**Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms**



**Figure 4. Diode reverse recovery test circuit & waveforms**



## Ordering Information

Package Type	Units/ Reel	Reels / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO252-P	2500	2	5000	5	25000

## Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFS130N06DF	TO252	yes	yes	yes

## Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Oriental Semiconductor hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

For further information on technology, delivery terms and conditions and prices, please contact the Oriental Semiconductor sales representatives ([www.orientalsemi.com](http://www.orientalsemi.com)).

© Oriental Semiconductor Co.,Ltd. All Rights Reserved 